

# CR12CM-12A

600V - 12A - Thyristor

Medium Power Use

R07DS1035EJ0500

Rev.5.00

Jan. 15, 2019

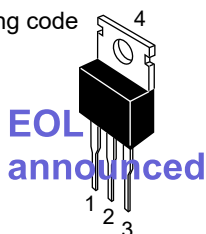
## Features

- $I_T(AV)$  : 12 A
- $V_{DRM}$  : 600 V
- $I_{GT}$ : 30 mA
- Non-insulated Type
- Planar Passivation Type

## Outline

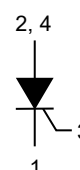
RENESAS Package code: PRSS0004AG-A  
(Package name: TO-220AB)

Ordering code  
#BB0



RENESAS Package code: PRSS0004AT-A  
(Package name: TO-220ABA)

Ordering code  
#BH0



1. Cathode
2. Anode
3. Gate
4. Anode

## Application

Power supply, motor control, heater control and other general purpose applications.

## Maximum Ratings

| Parameter                           | Symbol    | Voltage class | Unit |
|-------------------------------------|-----------|---------------|------|
|                                     |           | 12            |      |
| Repetitive peak reverse voltage     | $V_{RRM}$ | 600           | V    |
| Non-repetitive peak reverse voltage | $V_{RSM}$ | 720           | V    |
| DC reverse voltage                  | $V_R(DC)$ | 480           | V    |
| Repetitive peak off-state voltage   | $V_{DRM}$ | 600           | V    |
| DC off-state voltage                | $V_D(DC)$ | 480           | V    |

| Parameter                      | Symbol     | Ratings     | Unit             | Conditions                                                                                   |
|--------------------------------|------------|-------------|------------------|----------------------------------------------------------------------------------------------|
| RMS on-state current           | $I_T(RMS)$ | 18.8        | A                |                                                                                              |
| Average on-state current       | $I_T(AV)$  | 12          | A                | Commercial frequency, sine half wave<br>180°conduction, $T_c = 91^{\circ}C$ <sup>Note1</sup> |
| Surge on-state current         | $I_{TSM}$  | 360         | A                | 60 Hz sinewave 1 full cycle, peak value,<br>non-repetitive                                   |
| $I^2t$ for fusing              | $I^2t$     | 544         | A <sup>2</sup> s | Value corresponding to 1 cycle of half wave<br>60 Hz, surge on-state current                 |
| Peak gate power dissipation    | $P_{GM}$   | 5           | W                |                                                                                              |
| Average gate power dissipation | $P_G(AV)$  | 0.5         | W                |                                                                                              |
| Peak gate forward voltage      | $V_{FGM}$  | 6           | V                |                                                                                              |
| Peak gate reverse voltage      | $V_{RGM}$  | 10          | V                |                                                                                              |
| Peak gate forward current      | $I_{FGM}$  | 2           | A                |                                                                                              |
| Junction temperature           | $T_j$      | -40 to +125 | °C               |                                                                                              |
| Storage temperature            | $T_{stg}$  | -40 to +125 | °C               |                                                                                              |

## Electrical Characteristics

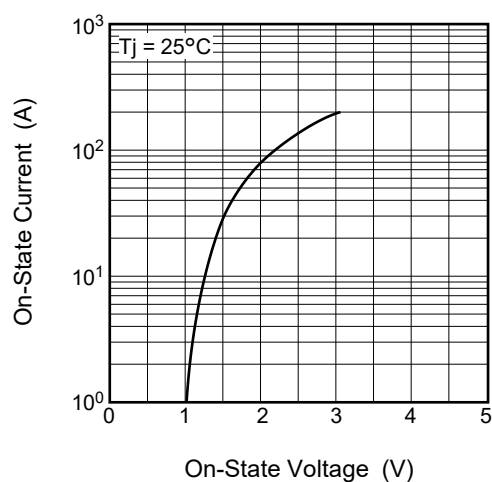
| Parameter                         | Symbol        | Min. | Typ. | Max. | Unit                 | Test conditions                                                           |
|-----------------------------------|---------------|------|------|------|----------------------|---------------------------------------------------------------------------|
| Repetitive peak reverse current   | $I_{RRM}$     | —    | —    | 2.0  | mA                   | $T_J = 125^{\circ}\text{C}$ , $V_{RRM}$ applied                           |
| Repetitive peak off-state current | $I_{DRM}$     | —    | —    | 2.0  | mA                   | $T_J = 125^{\circ}\text{C}$ , $V_{DRM}$ applied                           |
| On-state voltage                  | $V_{TM}$      | —    | —    | 1.6  | V                    | $T_C = 25^{\circ}\text{C}$ , $I_{TM} = 40\text{ A}$ , instantaneous value |
| Gate trigger voltage              | $V_{GT}$      | —    | —    | 1.5  | V                    | $T_J = 25^{\circ}\text{C}$ , $V_D = 6\text{ V}$ , $I_T = 1\text{ A}$      |
| Gate non-trigger voltage          | $V_{GD}$      | 0.2  | —    | —    | V                    | $T_J = 125^{\circ}\text{C}$ , $V_D = 1/2 V_{DRM}$                         |
| Gate trigger current              | $I_{GT}$      | —    | —    | 30   | mA                   | $T_J = 25^{\circ}\text{C}$ , $V_D = 6\text{ V}$ , $I_T = 1\text{ A}$      |
| Holding current                   | $I_H$         | —    | 30   | —    | mA                   | $T_J = 25^{\circ}\text{C}$ , $V_D = 12\text{ V}$                          |
| Thermal resistance                | $R_{th(j-c)}$ | —    | —    | 1.2  | $^{\circ}\text{C/W}$ | Junction to case <sup>Note1</sup> <sup>Note2</sup>                        |

Notes: 1. Case temperature is measured at anode tab 1.5 mm away from the molded case.

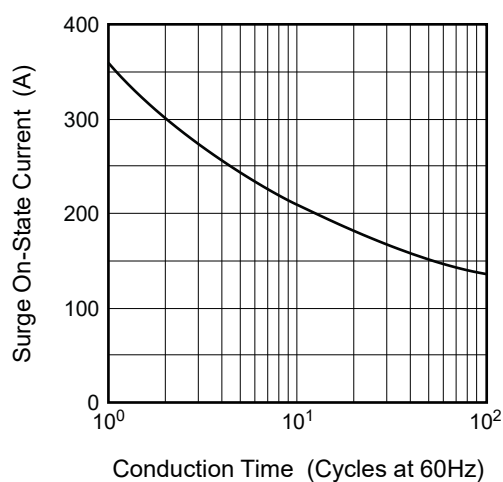
2. The contact thermal resistance  $R_{th(c-f)}$  in case of greasing is  $1.0^{\circ}\text{C/W}$ .

## Performance Curves

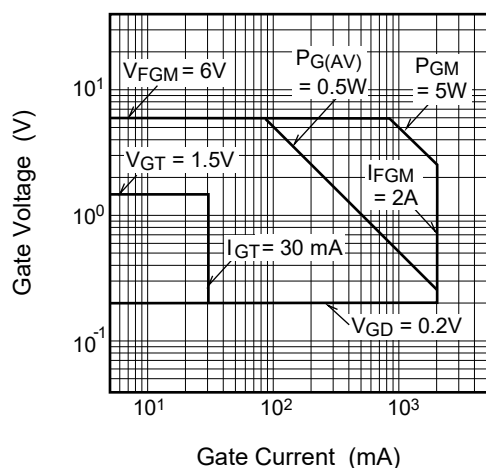
Maximum On-State Characteristics



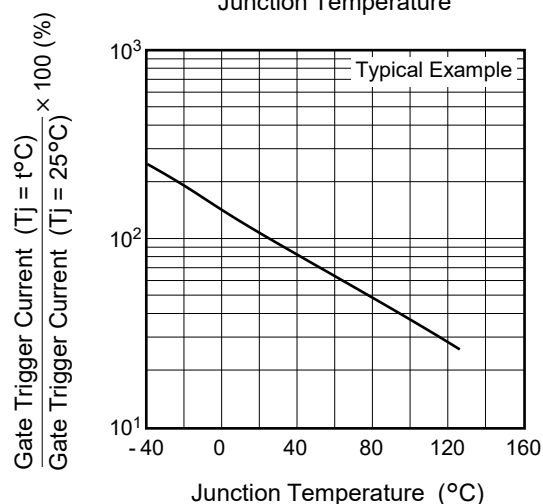
Rated Surge On-State Current



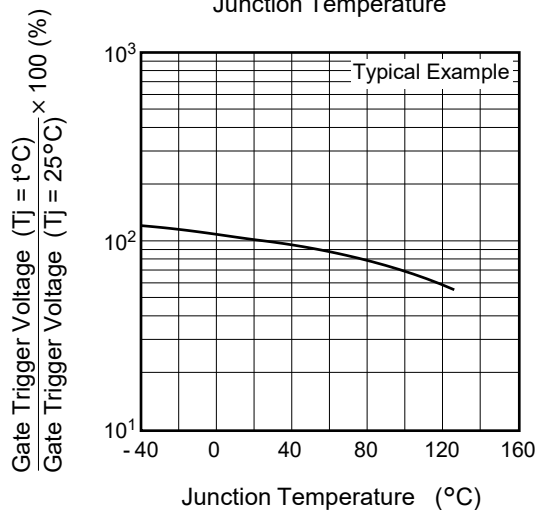
Gate Characteristics



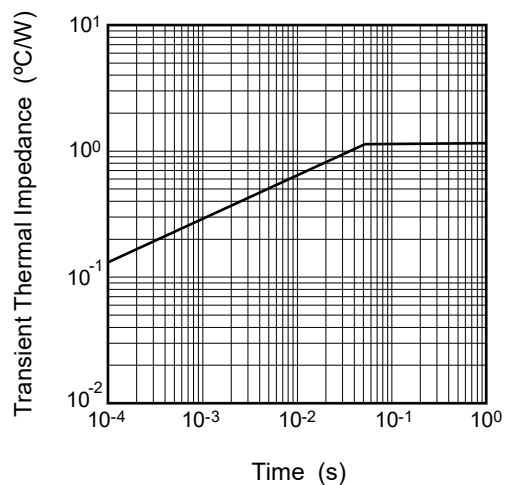
Gate Trigger Current vs. Junction Temperature



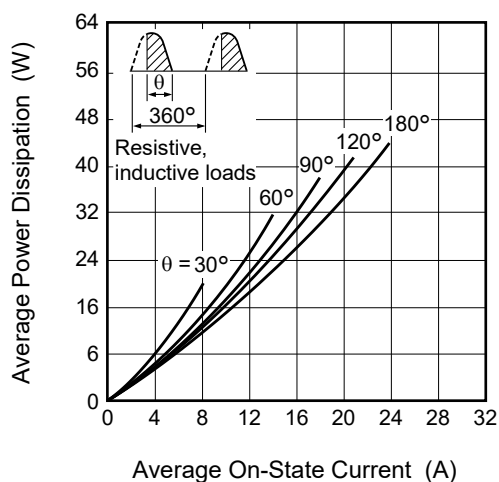
Gate Trigger Voltage vs. Junction Temperature



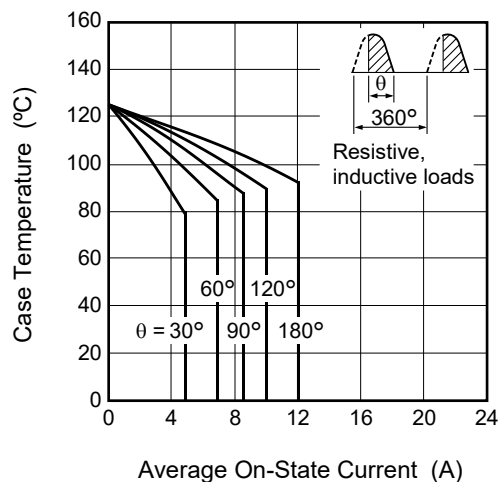
Maximum Transient Thermal Impedance Characteristics (Junction to case)



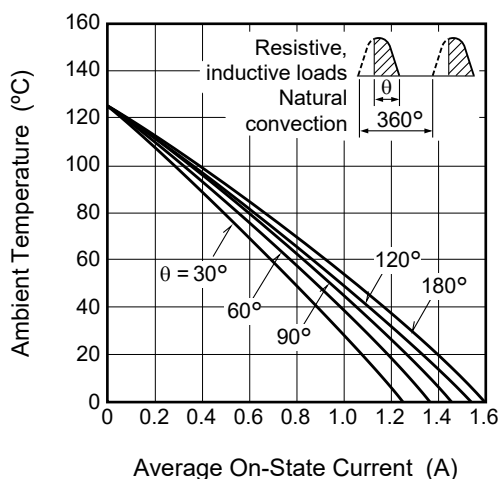
Maximum Average Power Dissipation  
(Single-Phase Half Wave)



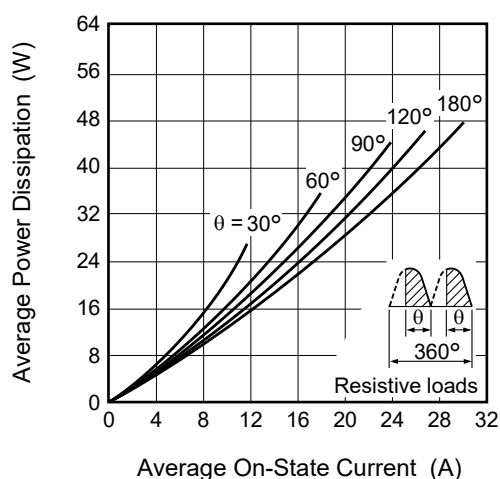
Allowable Case Temperature vs.  
Average On-State Current  
(Single-Phase Half Wave)



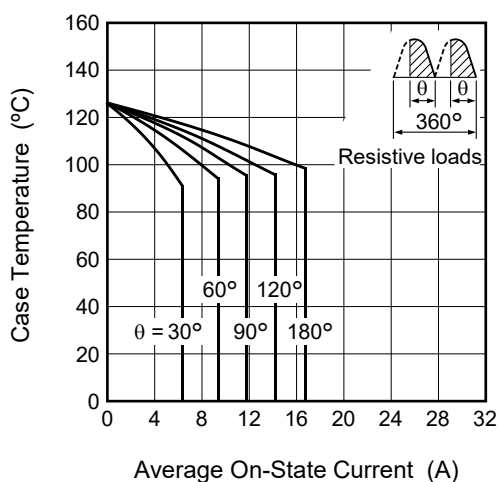
Allowable Ambient Temperature vs.  
Average On-State Current  
(Single-Phase Half Wave)



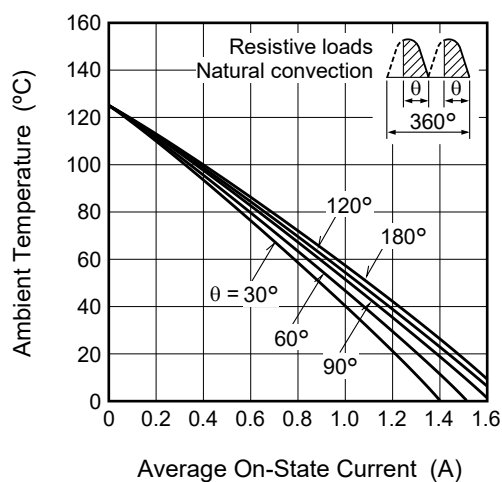
Maximum Average Power Dissipation  
(Single-Phase Full Wave)

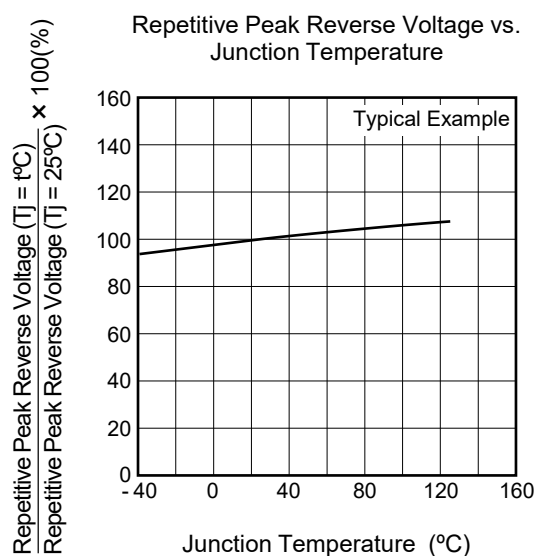
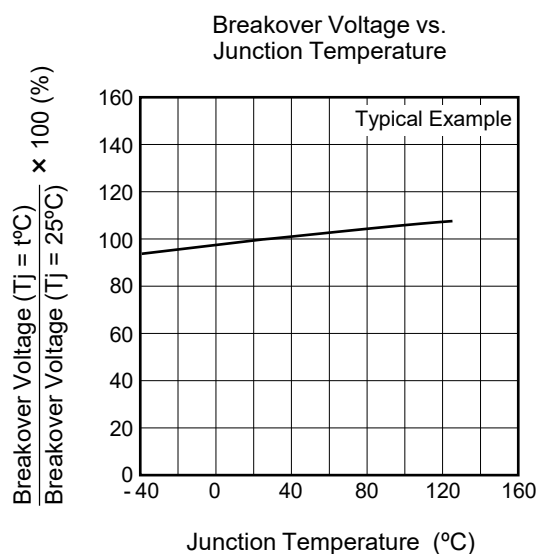
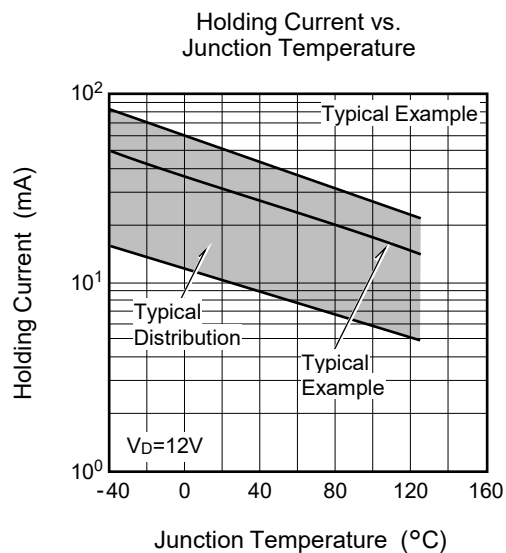
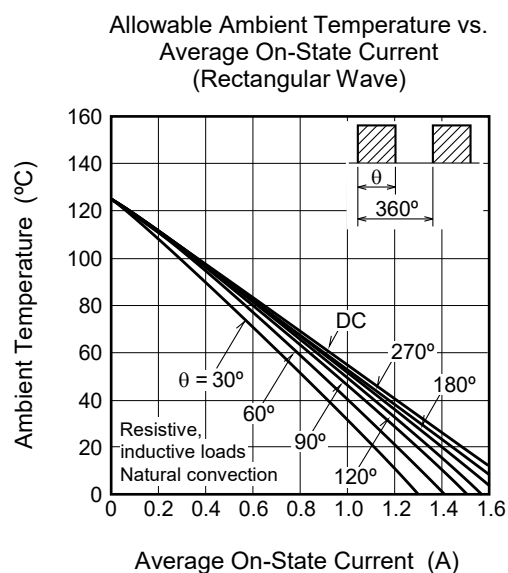
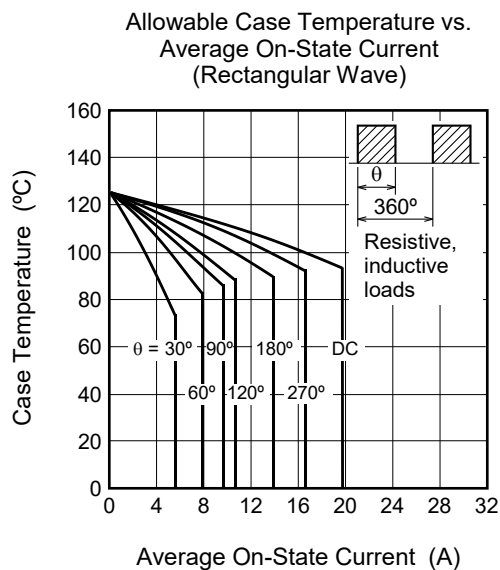
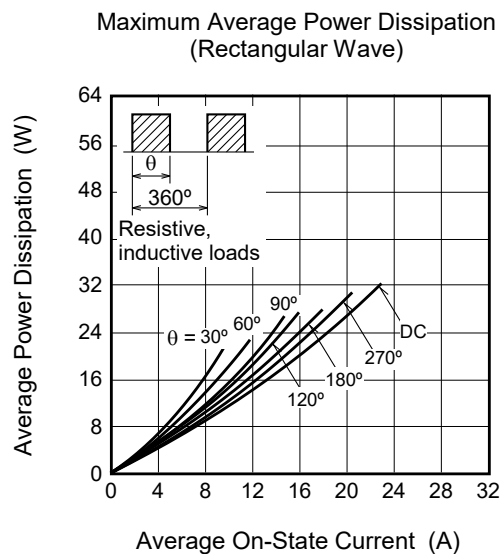


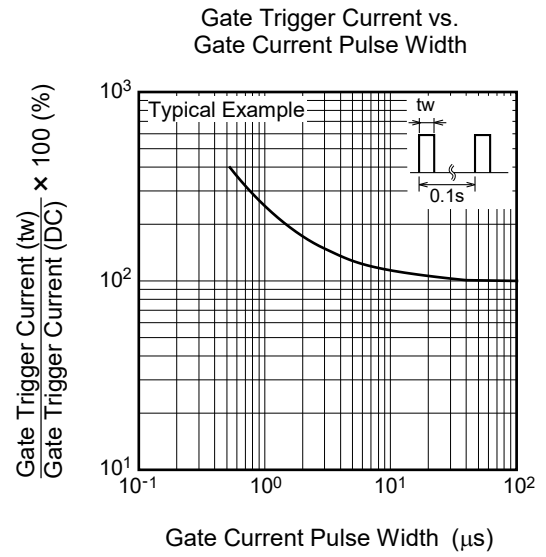
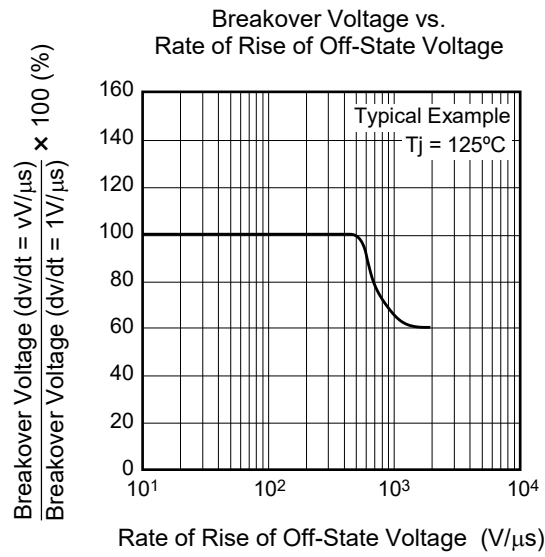
Allowable Case Temperature vs.  
Average On-State Current  
(Single-Phase Full Wave)



Allowable Ambient Temperature vs.  
Average On-State Current  
(Single-Phase Full Wave)

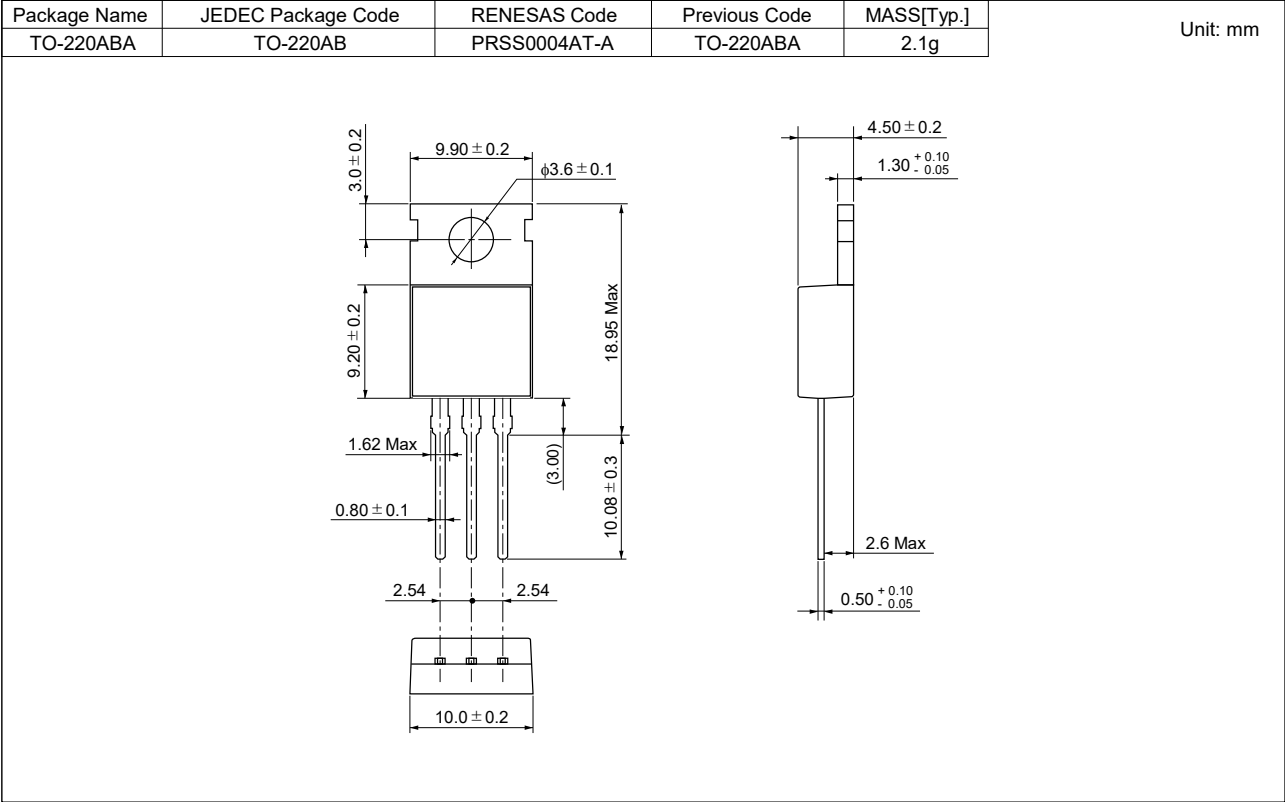




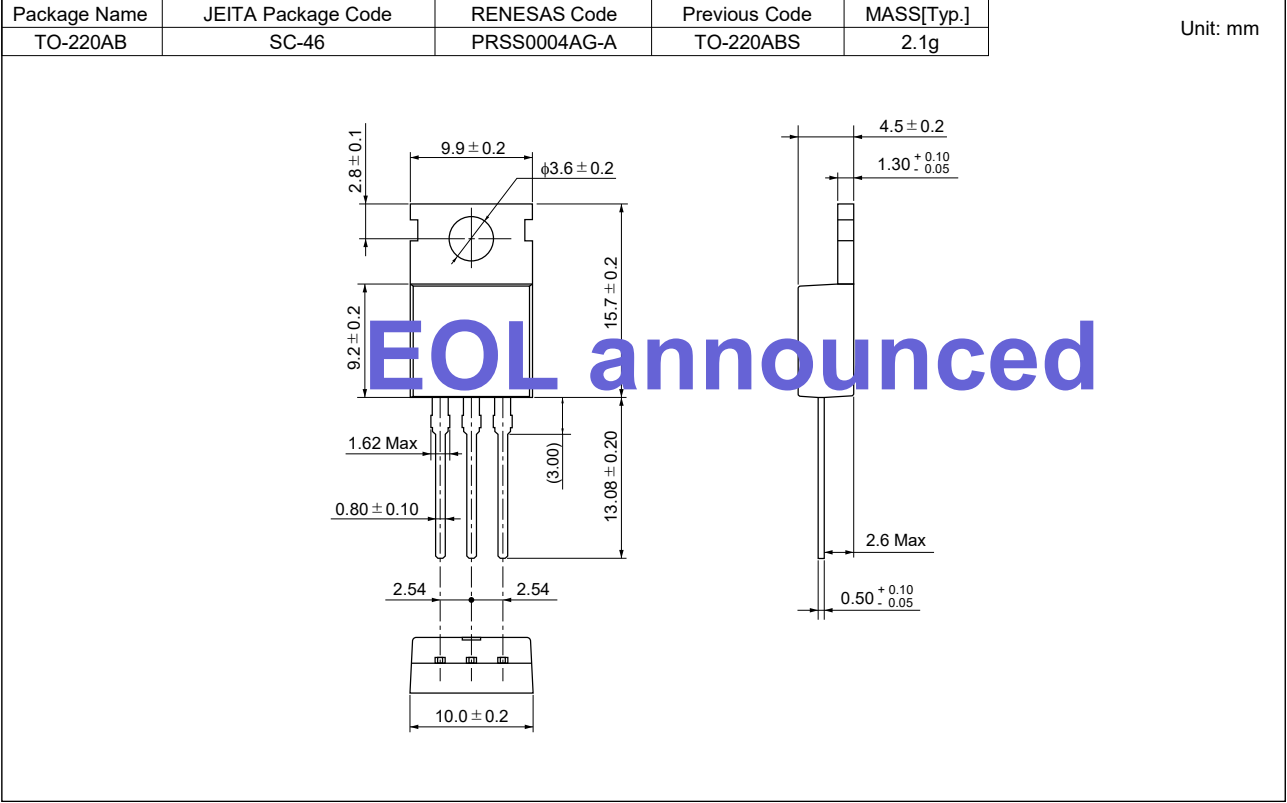


Package Dimensions

Ordering code: #BH0



Ordering code: #BB0



**Ordering Information**

| Orderable Part Number | Package   | Quantity <sup>Note3</sup> | Remark        | Status          |
|-----------------------|-----------|---------------------------|---------------|-----------------|
| CR12CM-12A#BH0        | TO-220ABA | 50 pcs./ tube             | Straight type | Mass Production |
| CR12CM-12A#BB0        | TO-220ABS | 50 pcs./ tube             | Straight type | EOL announced   |

Notes: 3. Please confirm the specification about the shipping in detail.

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